High voltage, high current Darlington transistor array BA12001B/BA12002/BA12003B/BA12003BF/ BA12004B

The BA12001B, BA12002, BA12003B, BA12003BF, and BA12004B are high current transistor arrays featuring high voltage withstand resistance and consisting of seven circuits of Darlington transistors.

Because it incorporates built-in surge-absorbing diodes and base current-control resistors needed when using inductive loads such as relay coils, attachments can be kept to a minimum.

With an output withstanding voltage as high as 60V (BA12001B, BA12003B, BA12003BF, and BA12004B) and an output current (sink current) of 500mA, this product is ideal for use with various drivers and as an interface with other elements.

Applications

Drivers for LEDs, lamps, relays and solenoids Interface with other elements

Features

- 1) High output current. (lour = 500mA max.)
- High output voltage withstand resistance. (Vout = 50V max.)
- 3) Seven Darlington transistors built in.
- Equipped with output surge-absorbing clamp diode.

Block diagram



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BA12001B/BA12002/BA12003B/BA12003BF/BA12004B

Internal circuit configuration diagram



●Absolute maximum ratings (Ta=25℃)

Para	ameter	Symbol	Limits	Unit	
Power supply voltage	other than BA12002	М.	60	- v	
	BA12002	Vce	50		
Input voltage	other than BA12001B	Vin	-0.5~30	v	
Input current	BA12001B	lin	25	mA / unit	
Output current		Ιουτ	500	mA / unit	
Ground pin current		IGND	2.3 *1	A	
Power dissipation	DIP package		1250 *2	mW	
	SOP package	Pd –	625 * ³		
Diode reverse voltage		VR	60	V	
Diode forward current		٩l	500	mA	
Operating temperature		Topr	-25~75	ĉ	
Storage temperature		Tstg	-55~150	Ċ	

* 1 Pulse width \leq 20 ms, duty cycle \leq 10%, same current for all 7 circuits

*2 Reduced by 10 mW for each increase in Ta of 1°C over 25°C .

*3 Reduced by 50 mW for each increase in Ta of 1°C over 25°C .



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Transistor arrays

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BA12001B/BA12002/BA12003B/BA12003BF/BA12004B

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●Recommended operating conditions (Ta=25℃)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions
Output current		ίουτ	-	_	350	mΑ	Fig.8, 9
Power supply voltage	Other than BA12002	Vce	_	-	55	v	-
	BA12002		_	_	50		-
Input voltage (excluding BA12001B)		Vin	-	-	30	V	—
Input current (BA12001B only)		lin	_	-	25	mA / unit	-

●Electrical characteristics (unless otherwise noted, Ta=25℃)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	Measuremen Circuit	
Output leakage current		l.		0	10	μA	Vce=50V	Fig.4	
DC current gain		h⊧ε	1000	2400	—	v	Vc∈=2V, lour=350mA	Fig.4	
Output saturation voltage		Vce(sat)		0.94	1.1	v	louτ=100mA, lin=250 μA	Fig.4	
				1.14	1.3		lout=200mA, lin=350 μA	Fig.4	
				1.46	1.6		lout=350mA, lin=500 μA	Fig.4	
	BA12002			10.2	11	v	Vce=2V, lout=100mA	Fig.4	
	BA12003B/BF			1.75	2				
	BA12004B			2.53	5				
	BA12002	Vin		10.4	12	v	Vce=2V, lout=200mA	Fig.4	
	BA12003B/BF			1.91	2.4				
	BA12004B			2.75	6				
	BA12002	Vin		10.7	13.5	v	Vce=2V, lout=350mA	Fig.4	
	BA12003B/BF			2.17	3.4				
	BA12004B			3.27	8				
Input current	BA12002	- - - -	-	0.88	1.3	mA	V _{IN} =17V		
	BA12003B/BF			0.90	1.35		VIN=3.85V	Fig.4	
	BA12004B			0.39	0.5		V _{IN} =5V		
Diode reverse current		le le		0	50	μA	V _R =50V	Fig.4	
Diode forward voltage		VF	.—	1.73	2	v	l⊧=350mA	Fig.4	
Input capacitance		CIN		30		pF	VIN=0V, f=1MHz	Fig.4	

Note: Input voltage and input current for BA12001 vary based on external resistor.

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BA12001B/BA12002/BA12003B/BA12003BF/BA12004B

VCE (sat)

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VCE(sat)

OPEN

Measurement circuits



(4) Input current IN





(2) DC current gain

Output saturation voltage



(6) Diode forward voltage



(7) Input capacitance CiN



Fig. 4

Application example



Fig. 5

Reference items when using in application

The BA12001B is a transistor array which can be directly coupled to a general logic circuit such as PMOS, CMOS, or TTL.

Because the base current is limited to 25mA, a current limiting resistor needs to be connected in series with the input.

The BA12002 is designed for direct coupling with a 14 to 25V system PMOS. In order to limit the input current, a level shift diode (7V) and resistor are connected in series to each of the inputs.

The BA12003B/BF can be coupled directly to TTL or CMOS output (when operating at 5V). In order to limit the input current to a stable value, resistors are connected in series to each of the inputs.

The BA12004B is designed for direct coupling to CMOS or PMOS output using a 6 to 15V power supply voltage. In order to limit the input current to a stable value, resistors are connected in series to each of the inputs.

The load for each of these products should be connected between the driver output and the power supply. To protect the IC from excessive swing voltage, the COM pin (Pin 9) should be connected to the power supply.

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arrays

Transistor

BA12001B/BA12002/BA12003B/BA12003BF/BA12004B



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